NXP USA Inc. - <u>MPC8358CVVAGDG Datasheet</u>





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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Obsolete
PowerPC e300
1 Core, 32-Bit
400MHz
Communications; QUICC Engine
DDR, DDR2
No
-
10/100/1000Mbps (1)
-
USB 1.x (1)
1.8V, 2.5V, 3.3V
-40°C ~ 105°C (TA)
-
740-LBGA
740-TBGA (37.5x37.5)
https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8358cvvagdg

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wide range of protocols including ATM, Ethernet, HDLC, and POS. The QUICC Engine module's enhanced interworking eases the transition and reduces investment costs from ATM to IP based systems. The other major features include a dual DDR SDRAM memory controller for the MPC8360E, which allows equipment providers to partition system parameters and data in an extremely efficient way, such as using one 32-bit DDR memory controller for control plane processing and the other for data plane processing. The MPC8358E has a single DDR SDRAM memory controller. The MPC8360E/58E also offers a 32-bit PCI controller, a flexible local bus, and a dedicated security engine.

This figure shows the MPC8360Eblock diagram.



Figure 1. MPC8360E Block Diagram

Characteristic	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I^2C , SPI, and JTAG I/O voltage	OV _{DD}	3.3 V ± 330 mV	V	_
Junction temperature	TJ	0 to 105 -40 to 105	°C	2

Table 2. Recommended Operating Conditions (continued)

Notes:

- 1. GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
- The operating conditions for junction temperature, T_J, on the 600/333/400 MHz and 500/333/500 MHz on rev. 2.0 silicon is 0° to 70 °C. Refer to Errata General9 in *Chip Errata for the MPC8360E, Rev. 1*.
- 3. For more information on Part Numbering, refer to Table 80.

This figure shows the undershoot and overshoot voltages at the interfaces of the device.



1. Note that $t_{\mbox{interface}}$ refers to the clock period associated with the bus clock interface.

Figure 3. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$



DDR and DDR2 SDRAM AC Electrical Characteristics

Parameter/Condition	Symbol Min		Мах	Unit	Notes
Input high voltage	V _{IH}	V _{IH} MV _{REF} + 0.18		V	—
Input low voltage	V _{IL}	V _{IL} –0.3 M		V	—
Output leakage current	I _{OZ}	—	±10	μA	4
Output high current (V _{OUT} = 1.95 V)	I _{ОН}	I _{OH} –15.2		mA	—
Output low current (V _{OUT} = 0.35 V)	I _{OL}	15.2	_	mA	—
MV _{REF} input leakage current	I _{VREF}	—	±10	μA	—
Input current (0 V ≰⁄ _{IN} ≤OV _{DD})	I _{IN}	—	±10	μA	_

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

- 2. MV_{REF} is expected to be equal to $0.5 \times GV_{DD}$, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
- 3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
- 4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

This table provides the DDR capacitance when $GV_{DD}(typ) = 2.5$ V.

Table 17. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
Input/output capacitance: DQ, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C _{DIO}	_	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = $GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM interface when $GV_{DD}(typ) = 1.8 V$.

Table 18. DDR2 SDRAM Input AC Timing Specifications for GV_{DD}(typ) = 1.8 V

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%.

Parameter	Symbol	Min Max		Unit	Notes
AC input low voltage	V _{IL}	—	MV _{REF} – 0.25	V	—
AC input high voltage	V _{IH}	MV _{REF} + 0.25	_	V	_



DDR and DDR2 SDRAM AC Electrical Characteristics

This table provides the input AC timing specifications for the DDR SDRAM interface when $GV_{DD}(typ) = 2.5 \text{ V}$.

Table 19. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min Max		Unit	Notes
AC input low voltage	V _{IL}	—	MV _{REF} – 0.31	V	—
AC input high voltage	V _{IH}	MV _{REF} + 0.31	_	V	_

Table 20. DDR and DDR2 SDRAM Input AC Timing Specifications Mode

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol	Min	Мах	Unit	Notes
MDQS—MDQ/MECC input skew per byte 333 MHz 266 MHz 200 MHz	t _{DISKEW}	-750 -1125 -1250	750 1125 1250	ps	1, 2

Notes:

1. AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.

Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 ≤n ≤7) or ECC (MECC[{0...7}] if n = 8).

This figure shows the input timing diagram for the DDR controller.



Figure 6. DDR Input Timing Diagram



DDR and DDR2 SDRAM AC Electrical Characteristics

This figure provides the AC test load for the DDR bus.



Figure 8. DDR AC Test Load

Table 22. DDR and DDR2 SDRAM Measurement Conditions

Symbol	DDR	DDR2	Unit	Notes
V _{TH}	MV _{REF} ± 0.31 V	MV _{REF} ± 0.25 V	V	1
V _{OUT}	$0.5 \times \text{ GV}_{\text{DD}}$	$0.5 \times \text{ GV}_{\text{DD}}$	V	2

Notes:

1. Data input threshold measurement point.

2. Data output measurement point.

This figure shows the DDR SDRAM output timing diagram for source synchronous mode.



Figure 9. DDR SDRAM Output Timing Diagram for Source Synchronous Mode



8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

This table provides the RMII transmit AC timing specifications.

Table 31. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
REF_CLK clock	t _{RMX}	_	20	—	ns
REF_CLK duty cycle	t _{RMXH} /t _{RMX}	35	_	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	t _{RMTKHDX} t _{RMTKHDV}	2	_	 10	ns
REF_CLK data clock rise time	t _{RMXR}	1.0	_	4.0	ns
REF_CLK data clock fall time	t _{RMXF}	1.0		4.0	ns

Note:

The symbols used for timing specifications follow the pattern of t<sub>(first three letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{RMTKHDX} symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub>

This figure shows the RMII transmit AC timing diagram.



Figure 15. RMII Transmit AC Timing Diagram

8.2.3.2 RMII Receive AC Timing Specifications

This table provides the RMII receive AC timing specifications.

Table 32. RMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
REF_CLK clock period	t _{RMX}	—	20	—	ns
REF_CLK duty cycle	t _{RMXH} /t _{RMX}	35	—	65	%



8.2.4.1 TBI Transmit AC Timing Specifications

This table provides the TBI transmit AC timing specifications.

Table 33. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit	Notes
GTX_CLK clock period	t _{TTX}	_	8.0	_	ns	—
GTX_CLK duty cycle	t _{TTXH} /t _{TTX}	40	—	60	%	—
GTX_CLK to TBI data TCG[9:0] delay	t _{TTKHDX} t _{TTKHDV}	1.0	—	 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	t _{TTXR}	_	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	t _{TTXF}	_	_	1.0	ns	—
GTX_CLK125 reference clock period	t _{G125}	_	8.0	_	ns	2
GTX_CLK125 reference clock duty cycle	t _{G125H} /t _{G125}	45	—	55	ns	—

Notes:

- The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the invalid state (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- 2. This symbol is used to represent the external GTX_CLK125 and does not follow the original symbol naming convention.
- 3. In rev. 2.0 silicon, due to errata, t_{TTKHDX} minimum is 0.7 ns for UCC1. Refer to Errata QE_ENET19 in Chip Errata for the MPC8360E, Rev. 1.

This figure shows the TBI transmit AC timing diagram.



Figure 18. TBI Transmit AC Timing Diagram

Local Bus AC Electrical Specifications

Parameter	Symbol ¹	Min	Max	Unit	Notes
Local bus clock to output valid	t _{LBKHOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ}		4	ns	8

Table 41. Local Bus General Timing Parameters—DLL Bypass Mode⁹ (continued)

Notes:

- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the to the output (O) going invalid (X) or output hold time.
 </sub>
- 2. All timings are in reference to falling edge of LCLK0 (for all outputs and for LGTA and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
- 3. All signals are measured from OV_{DD}/2 of the rising/falling edge of LCLK0 to 0.4 × OV_{DD} of the signal in question for 3.3-V signaling levels.
- 4. Input timings are measured at the pin.
- 5. t_{LBOTOT1} should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
- t_{LBOTOT2} should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
- 7. t_{LBOTOT3} should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
- 8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

This figure provides the AC test load for the local bus.



Figure 22. Local Bus C Test Load



Local Bus AC Electrical Specifications



Figure 25. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (DLL Enabled)





10.2 JTAG AC Electrical Characteristics

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface of the device.

This table provides the JTAG AC timing specifications as defined in Figure 30 through Figure 33.

Table 43. JTAG AC Timing Specifications (Independent of CLKIN)¹

At recommended operating conditions (see Table 2).

Parameter	Symbol ²	Min	Max	Unit	Notes
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	_
JTAG external clock duty cycle	t _{JTKHKL} /t _{JTG}	45	55	%	_
JTAG external clock rise and fall times	t _{JTGR} & t _{JTGF}	0	2	ns	_
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} t _{JTIVKH}	4 4	_	ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	10 10	_	ns	4
Valid times: Boundary-scan data TDO	t _{JTKLDV} t _{JTKLOV}	2 2	11 11	ns	5
Output hold times: Boundary-scan data TDO	t _{jtkldx} t _{jtklox}	2 2	_	ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t _{JTKLDZ} t _{JTKLOZ}	2 2	19 9	ns	5, 6

Notes:

- 2. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- 3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.
- 4. Non-JTAG signal input timing with respect to t_{TCLK}.
- 5. Non-JTAG signal output timing with respect to t_{TCLK}.
- 6. Guaranteed by design and characterization.

All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Figure 22). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.



I2C AC Electrical Specifications

11.2 I²C AC Electrical Specifications

This table provides the AC timing parameters for the I²C interface of the device.

Table 45. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 44).

Parameter	Symbol ¹	Min	Max	Unit	Note
SCL clock frequency	f _{I2C}	0	400	kHz	2
Low period of the SCL clock	t _{I2CL}	1.3	_	μs	—
High period of the SCL clock	t _{I2CH}	0.6	_	μs	—
Setup time for a repeated START condition	t _{I2SVKH}	0.6	_	μs	—
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t _{I2SXKL}	0.6	_	μs	_
Data setup time	t _{I2DVKH}	100	_	ns	3
Data hold time: CBUS compatible masters I ² C bus devices	t _{I2DXKL}	$\frac{1}{0^2}$	 0.9 ³	μs	—
Rise time of both SDA and SCL signals	t _{I2CR}	20 + 0.1 C _b ⁴	300	ns	—
Fall time of both SDA and SCL signals	t _{I2CF}	20 + 0.1 C _b ⁴	300	ns	—
Set-up time for STOP condition	t _{I2PVKH}	0.6	_	μs	—
Bus free time between a STOP and START condition	t _{I2KHDX}	1.3	_	μs	—
Noise margin at the LOW level for each connected device (including hysteresis)	V _{NL}	$0.1 \times \text{OV}_{\text{DD}}$	_	V	_
Noise margin at the HIGH level for each connected device (including hysteresis)	V _{NH}	$0.2 \times \text{OV}_{\text{DD}}$	_	V	_

Notes:

1. The symbols used for timing specifications follow the pattern of t_{(first two letters of functional}

block)(signal)(state)(reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

 The device provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH} min of the SCL signal) to bridge the undefined region of the falling edge of SCL.

3. The maximum t_{12DVKH} has only to be met if the device does not stretch the LOW period (t_{12CL}) of the SCL signal.

4. C_B = capacitance of one bus line in pF.



Table 66. MPC8360E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_DEVSEL/CE_PF[16]	E26	I/O	OV _{DD}	5
PCI_IDSEL/CE_PF[17]	F22	I/O	OV _{DD}	
PCI_SERR/CE_PF[18]	B29	I/O	OV _{DD}	5
PCI_PERR/CE_PF[19]	A29	I/O	OV _{DD}	5
PCI_REQ[0]/CE_PF[20]	F19	I/O	LV _{DD} 2	—
PCI_REQ[1]/CPCI_HS_ES/ CE_PF[21]	A21	I/O	LV _{DD} 2	—
PCI_REQ[2]/CE_PF[22]	C21	I/O	LV _{DD} 2	
PCI_GNT[0]/CE_PF[23]	E20	I/O	LV _{DD} 2	
PCI_GNT[1]/CPCI1_HS_LED/ CE_PF[24]	B20	I/O	LV _{DD} 2	
PCI_GNT[2]/CPCI1_HS_ENUM/ CE_PF[25]	C20	I/O	LV _{DD} 2	
PCI_MODE	D36	Ι	OV _{DD}	—
M66EN/CE_PF[4]	B37	I/O	OV _{DD}	
	Local Bus Controller Interface			
LAD[0:31]	N32, N33, N35, N36, P37, P32, P34, R36, R35, R34, R33, T37, T35, T34, T33, U37, T32, U36, U34, V36, V35, W37, W35, V33, V32, W34, Y36, W32, AA37, Y33, AA35, AA34	I/O	OV _{DD}	_
LDP[0]/CKSTOP_OUT	AB37	I/O	OV _{DD}	
LDP[1]/CKSTOP_IN	AB36	I/O	OV _{DD}	
LDP[2]/LCS[6]	AB35	I/O	OV _{DD}	
LDP[3]/LCS[7]	AA33	I/O	OV _{DD}	
LA[27:31]	AC37, AA32, AC36, AC34, AD36	0	OV _{DD}	
LCS[0:5]	AD33, AG37, AF34, AE33, AD32, AH37	0	OV_{DD}	
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AG35, AG34, AH36, AE32	0	OV_{DD}	
LBCTL	AD35	0	OV_{DD}	
LALE	M37	0	OV_{DD}	
LGPL0/LSDA10/cfg_reset_source0	AB32	I/O	OV_{DD}	
LGPL1/LSDWE/cfg_reset_source1	AE37	I/O	OV_{DD}	
LGPL2/LSDRAS/LOE	AC33	0	OV_{DD}	
LGPL3/LSDCAS/cfg_reset_source2	AD34	I/O	OV_{DD}	
LGPL4/LGTA/LUPWAIT/LPBSE	AE35	I/O	OV_{DD}	
LGPL5/cfg_clkin_div	AF36	I/O	OV_{DD}	
LCKE	G36	0	OV _{DD}	—
LCLK[0]	J33	0	OV _{DD}	—
LCLK[1]/LCS[6]	J34	0	OV _{DD}	—



Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV _{DD} 0	D5, D6	Power for UCC1 Ethernet interface (2.5 V, 3.3 V)	LV _{DD} 0	
LV _{DD} 1	C17, D16	Power for UCC2 Ethernet interface option 1 (2.5 V, 3.3 V)	LV _{DD} 1	9
LV _{DD} 2	B18, E21	Power for UCC2 Ethernet interface option 2 (2.5 V, 3.3 V)	LV _{DD} 2	9
V _{DD}	C36, D29, D35, E16, F9, F12, F15, F17, F18, F20, F21, F23, F25, F26, F29, F31, F32, F33, G6, J6, K32, M32, N6, P33, R6, R32, U32, V6, Y5, Y32, AB6, AB33, AD6, AF32, AK6, AL6, AM7, AM9, AM10, AM11, AM12, AM13, AM14, AM15, AM18, AM21, AM25, AM28, AM32, AN15, AN21, AN26, AU9, AU17	Power for core (1.2 V)	V _{DD}	_
OV _{DD}	A10, B9, B15, B32, C1, C12, C22, C29, D24, E3, E10, E27, G4, H35, J1, J35, K2, M4, N3, N34, R2, R37, T36, U2, U33, V4, V34, W3, Y35, Y37, AA1, AA36, AB2, AB34	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV _{DD}	_
MVREF1	AN20	I	DDR reference voltage	—
MVREF2	AU32	I	DDR reference voltage	_
SPARE1	B11	I/O	OV _{DD}	8
SPARE3	AH32		GV _{DD}	8
SPARE4	AU18	_	GV _{DD}	7
SPARE5	AP1	_	GV _{DD}	8

Table 66. MPC8360E TBGA Pinout Listing (continued)



Pinout Listings

clock. When the device is configured as a PCI agent device the CLKIN and the CFG_CLKIN_DIV signals should be tied to GND.

When the device is configured as a PCI host device (RCWH[PCIHOST] = 1) and PCI clock output is disabled (RCWH[PCICKDRV] = 0), clock distribution and balancing done externally on the board. Therefore, PCI_SYNC_IN is the primary input clock.

As shown in Figure 54 and Figure 55, the primary clock input (frequency) is multiplied by the QUICC Engine block phase-locked loop (PLL), the system PLL, and the clock unit to create the QUICC Engine clock (ce_clk), the coherent system bus clock (csb_clk), the internal DDRC1 controller clock ($ddr1_clk$), and the internal clock for the local bus interface unit and DDR2 memory controller (lb_clk).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

$$csb_clk = \{PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV)\} \times SPMF$$

In PCI host mode, PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV) is the CLKIN frequency; in PCI agent mode, CFG_CLKIN_DIV must be pulled down (low), so PCI_SYNC_IN \times (1 + CFG_CLKIN_DIV) is the PCI_CLK frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies up the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL) which is loaded at power-on reset or by one of the hard-coded reset options. See Chapter 4, "Reset, Clocking, and Initialization," in the *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for more information on the clock subsystem.

The *ce_clk* frequency is determined by the QUICC Engine PLL multiplication factor (RCWL[CEPMF) and the QUICC Engine PLL division factor (RCWL[CEPDF]) according to the following equation:

 $ce_clk = (primary clock input \times CEPMF) \div (1 + CEPDF)$

The internal *ddr1_clk* frequency is determined by the following equation:

 $ddr1_clk = csb_clk \times (1 + RCWL[DDR1CM])$

Note that the lb_clk clock frequency (for DDRC2) is determined by RCWL[LBCM]. The *internal ddr1_clk* frequency is not the external memory bus frequency; *ddr1_clk* passes through the DDRC1 clock divider (\div 2) to create the differential DDRC1 memory bus clock outputs (MEMC1_MCK and MEMC1_MCK). However, the data rate is the same frequency as *ddr1_clk*.

The internal *lb_clk* frequency is determined by the following equation:

 $lb_clk = csb_clk \times (1 + \text{RCWL[LBCM]})$

Note that *lb_clk* is not the external local bus or DDRC2 frequency; *lb_clk* passes through the a LB clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LB clock divider ratio is controlled by LCRR[CLKDIV].

Additionally, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset. This table specifies which units have a configurable clock frequency.

Unit	Default Frequency	Options
Security core	csb_clk/3	Off, <i>csb_clk</i> ¹ , <i>csb_clk</i> /2, <i>csb_clk</i> /3
PCI and DMA complex	csb_clk	Off, <i>csb_clk</i>

Table 68	Configurable	Clock	Units
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¹ With limitation, only for slow csb_clk rates, up to 166 MHz.

This table provides the operating frequencies for the TBGA package under recommended operating conditions (see Table 2). All frequency combinations shown in the table below may not be available. Maximum operating frequencies depend on the part





ordered, see Section 24.1, "Part Numbers Fully Addressed by this Document," for part ordering details and contact your Freescale sales representative or authorized distributor for more information.

Characteristic ¹	400 MHz	533 MHz	667 MHz ²	Unit
e300 core frequency (<i>core_clk</i>)	266–400	266–533	266–667	MHz
Coherent system bus frequency (<i>csb_clk</i>)	133–333			MHz
QUICC Engine frequency ³ (<i>ce_clk</i>)	266–500			MHz
DDR and DDR2 memory bus frequency (MCLK) ⁴	100–166.67			MHz
Local bus frequency (LCLK <i>n</i>) ⁵	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66.67			MHz
Security core maximum internal operating frequency	133 133 166			MHz

Table 69. Operating Frequencies for the TBGA Package

Notes:

- 1. The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.
- 2. The 667 MHz core frequency is based on a 1.3 V V_{DD} supply voltage.
- 3. The 500 MHz QE frequency is based on a 1.3 V V_{DD} supply voltage.
- 4. The DDR data rate is 2x the DDR memory bus frequency.
- 5. The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBCM]).

21.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] and RCWL[SVCOD] parameters. This table shows the multiplication factor encodings for the system PLL.

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11

Table 70. System PLL Multiplication Factors



Core PLL Configuration

21.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). This table shows the encodings for RCWL[COREPLL]. COREPLL values not listed in this table should be considered reserved.

RCWL[COREPLL]		core_clk:csb_clk	VCO divider	
0–1	2–5	6	Ratio	
nn	0000	n	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)	PLL bypassed (PLL off, <i>csb_clk</i> clocks core directly)
00	0001	0	1:1	÷2
01	0001	0	1:1	÷4
10	0001	0	1:1	÷8
11	0001	0	1:1	÷8
00	0001	1	1.5:1	÷2
01	0001	1	1.5:1	÷4
10	0001	1	1.5:1	÷8
11	0001	1	1.5:1	÷8
00	0010	0	2:1	÷2
01	0010	0	2:1	÷4
10	0010	0	2:1	÷8
11	0010	0	2:1	÷8
00	0010	1	2.5:1	÷2
01	0010	1	2.5:1	÷4
10	0010	1	2.5:1	÷8
11	0010	1	2.5:1	÷8
00	0011	0	3:1	÷2
01	0011	0	3:1	÷4
10	0011	0	3:1	÷8
11	0011	0	3:1	÷8

Table 73. e300 Core PLL Configuration

NOTE

Core VCO frequency = Core frequency \times VCO divider. The VCO divider (RCWL[COREPLL[0:1]]) must be set properly so that the core VCO frequency is in the range of 800–1800 MHz. Having a core frequency below the CSB frequency is not a possible option because the core frequency must be equal to or greater than the CSB frequency.



21.3 QUICC Engine Block PLL Configuration

The QUICC Engine block PLL is controlled by the RCWL[CEPMF], RCWL[CEPDF], and RCWL[CEVCOD] parameters. This table shows the multiplication factor encodings for the QUICC Engine block PLL.

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
00000	0	× 16
00001	0	Reserved
00010	0	× 2
00011	0	× 3
00100	0	× 4
00101	0	× 5
00110	0	× 6
00111	0	× 7
01000	0	× 8
01001	0	× 9
01010	0	× 10
01011	0	× 11
01100	0	× 12
01101	0	× 13
01110	0	× 14
01111	0	× 15
10000	0	× 16
10001	0	× 17
10010	0	× 18
10011	0	× 19
10100	0	× 20
10101	0	× 21
10110	0	× 22
10111	0	× 23
11000	0	× 24
11001	0	× 25
11010	0	× 26
11011	0	× 27
11100	0	× 28

Table 74. QUICC Engine Block PLL Multiplication Factors



QUICC Engine Block PLL Configuration

RCWL[CEPMF]	RCWL[CEPDF]	QUICC Engine PLL Multiplication Factor = RCWL[CEPMF]/ (1 + RCWL[CEPDF])
11101	0	× 29
11110	0	× 30
11111	0	× 31
00011	1	× 1.5
00101	1	× 2.5
00111	1	× 3.5
01001	1	× 4.5
01011	1	× 5.5
01101	1	× 6.5
01111	1	× 7.5
10001	1	× 8.5
10011	1	× 9.5
10101	1	× 10.5
10111	1	× 11.5
11001	1	× 12.5
11011	1	× 13.5
11101	1	× 14.5

Table 74. QUICC Engine Block PLL Multiplication Factors (continued)

Note:

1. Reserved modes are not listed.

The RCWL[CEVCOD] denotes the QUICC Engine Block PLL VCO internal frequency as shown in this table.

Table 75. QUICC Engine Block PLL VCO Divider

RCWL[CEVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider (RCWL[CEVCOD]) must be set properly so that the QUICC Engine block VCO frequency is in the range of 600–1400 MHz. The QUICC Engine block frequency is not restricted by the CSB and core frequencies. The CSB, core, and QUICC Engine block frequencies should be selected according to the performance requirements.

Suggested PLL Configurations

Conf No. ¹	SPMF	CORE PLL	CEPMF	CEPDF	Input Clock Freq (MHz)	CSB Freq (MHz)	Core Freq (MHz)	QUICC Engine Freq (MHz)	400 (MHz)	533 (MHz)	667 (MHz)
c5	æ	æ	10000	0	33	—	—	533		∞	8
c6	æ	æ	10001	0	33	—	—	566		_	8
66 MHz CLKIN/PCI_SYNC_IN Options											
s1h	0011	0000110	æ	æ	66	200	400	_	8	∞	8
s2h	0011	0000101	æ	æ	66	200	500	_	_	∞	8
s3h	0011	0000110	æ	æ	66	200	600	_	_	—	8
s4h	0100	0000011	æ	æ	66	266	400	_	8	∞	8
s5h	0100	0000100	æ	æ	66	266	533	_	_	∞	8
s6h	0100	0000101	æ	æ	66	266	667	_	_	—	8
s7h	0101	0000010	æ	æ	66	333	333	_	8	∞	8
s8h	0101	0000011	æ	æ	66	333	500	_	_	∞	8
s9h	0101	0000100	æ	æ	66	333	667	_		—	8
c1h	æ	æ	00101	0	66	—	—	333	~	∞	∞
c2h	æ	æ	00110	0	66	—	—	400	8	∞	8
c3h	æ	æ	00111	0	66	—	_	466		∞	8
c4h	æ	æ	01000	0	66	—	_	533		∞	8
c5h	æ	æ	01001	0	66	—	_	600		—	~

Table 76. Suggested PLL Configurations (continued)

Note:

1. The Conf No. consist of prefix, an index and a postfix. The prefix "s" and "c" stands for "syset" and "ce" respectively. The postfix "h" stands for "high input clock." The index is a serial number.

The following steps describe how to use above table. See Example 1.

- 2. Choose the up or down sections in the table according to input clock rate 33 MHz or 66 MHz.
- 3. Select a suitable CSB and core clock rates from Table 76. Copy the SPMF and CORE PLL configuration bits.
- 4. Select a suitable QUICC Engine block clock rate from Table 76. Copy the CEPMF and CEPDF configuration bits.
- 5. Insert the chosen SPMF, COREPLL, CEPMF and CEPDF to the RCWL fields, respectively.

Heat Sink Attachment



Millen Loroco 671 Ea San Jo Interne	nium Electronics (MEI) o Sites ast Brokaw Road se, CA 95112 et: www.mei-millennium.com	408-436-8770
Tyco F Chip C P.O. B Harris Interne	Electronics Coolers TM ox 3668 burg, PA 17105-3668 et: www.chipcoolers.com	800-522-6752
Wakef 33 Bri Pelhar Interne	ield Engineering dge St. n, NH 03076 et: www.wakefield.com	603-635-5102
Interface materi Chome 77 Dra Wobur Interne	al vendors include the following: erics, Inc. agon Ct. rn, MA 01888-4014 et: www.chomerics.com	781-935-4850
Dow-C Dow-C 2200 V Midlar Interne	Corning Corporation Corning Electronic Materials W. Salzburg Rd. nd, MI 48686-0997 et: www.dowcorning.com	800-248-2481
Shin-E 10028 Phoen Interne	Etsu MicroSi, Inc. S. 51st St. ix, AZ 85044 et: www.microsi.com	888-642-7674
The B 18930 Chanh Interne	ergquist Company West 78th St. assen, MN 55317 et: www.bergquistcompany.com	800-347-4572

22.3 Heat Sink Attachment

When attaching heat sinks to these devices, an interface material is required. The best method is to use thermal grease and a spring clip. The spring clip should connect to the printed-circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces which would lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. Recommended maximum force on the top of the package is 10 lb force (4.5 kg force). If an adhesive attachment is planned, the adhesive should be intended for attachment to painted or plastic surfaces and its performance verified under the application requirements.